Preliminary Data Sheet





Triple Junction TO-9

High Power Single-Mode and Multi-Mode SemiNex Lasers

- 12xx to 19xx nm Custom Wavelengths Available Lensed Options Available

ApplicationsOEM Medical

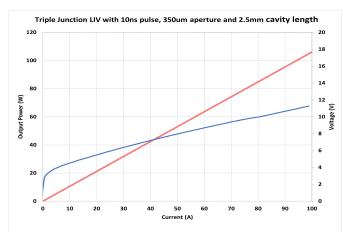
- Professional Medical Lidar •
 - Military / Aerospace
- Illumination

FeaturesCost effective

- Cost effective
 High Output Power
 High Dynamic Range
 High Efficiency
 Standard Low Cost Package

SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary we will further optimize the design of our InP laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.





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PI Sheet

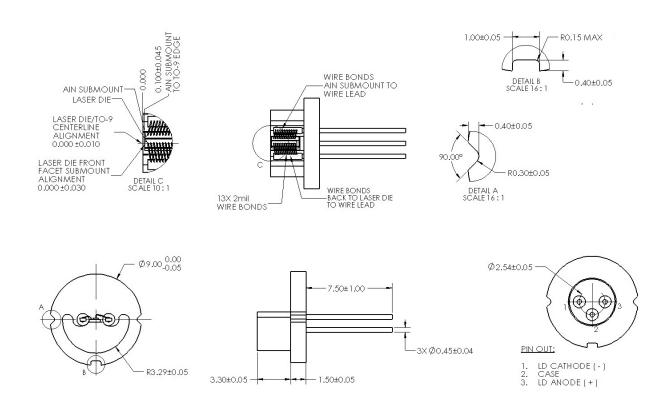






	Symbol	TO9-267	Units
Optical			
Navelength	λ _c	1550	nm (±20)
Dutput Power (<10ns)	P°	100.00	watts (±10%)
Dutput Power (150ns)	P•	75.00	watts (±10%)
Chip Cavity Length	CL	2500	μm
No. of Junctions		3	
Emitter Width	W	350	μm
Emitter Height	Н	10	μm
Spectral Width	δλ	22	nm 3dB
Slope Efficiency	η∘	1.00	W/A
Fast Axis Div.*	O_perp	28	deg FWHM
Slow Axis Div.	O_parallel	12	deg FWHM
Electrical			
Power Conversion Eff.	η	9	%
Dperating Current (<10ns)	I _{op}	100	A
Dperating Current (150ns)	I _{op}	75	A
Fhreshold Current	Ith	2	A
Operating Voltage	V _{op}	11	V
Mechanical			
Neight		0	g
Operating Temp.**		-40 to 85	°C
Storage Temp.		-40 to 85	°C

Specified values are rated at a constant heat sink temperature of 20°C.
**Specified operating conditions are based on 20C heat sink temperature. High temperature operation will reduce performance and MTTF.
Unless otherwise indicated all values are nominal.
Uncapped TO9 specifications assume heatsinking underneath laser chip.
Capped TO9 specifications assume heatsinking only on flat surface where pins extend.





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